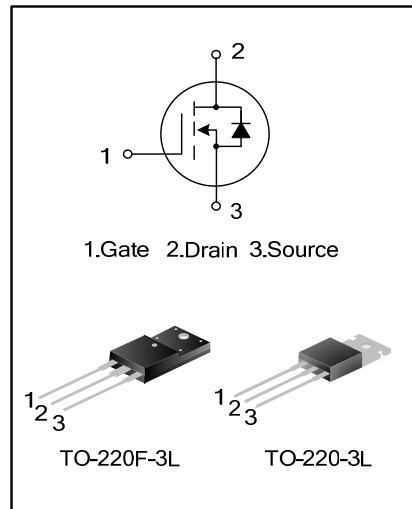


8A, 600V N-CHANNEL MOSFET

GENERAL DESCRIPTION

SVF8N60T/F is an N-channel enhancement mode power MOS field effect transistor which is produced using Silan proprietary F-Cell™ structure VDMOS technology. The improved planar stripe cell and the improved guarding ring terminal have been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode.

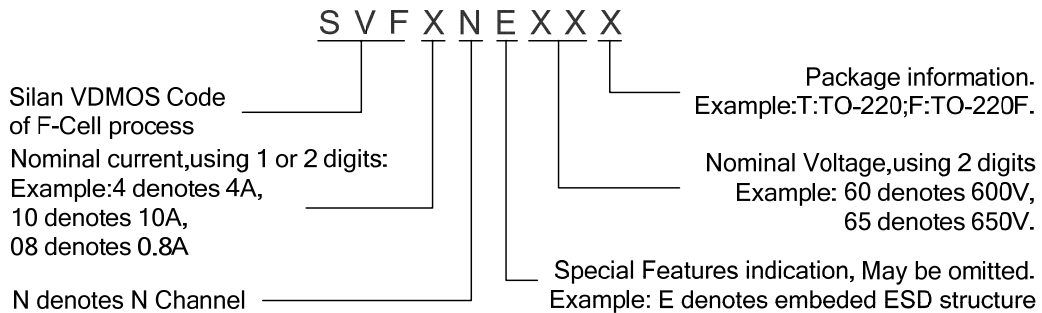
These devices are widely used in AC-DC power suppliers, DC-DC converters and H-bridge PWM motor drivers.



FEATURES

- * 8A,600V, $R_{DS(on)(typ.)}=0.96\Omega@V_{GS}=10V$
- * Low gate charge
- * Low Crss
- * Fast switching
- * Improved dv/dt capability

NOMENCLATURE



ORDERING INFORMATION

Part No.	Package	Marking	Material	packing
SVF8N60T	TO-220-3L	SVF8N60T	Pb free	Tube
SVF8N60F	TO-220F-3L	SVF8N60F	Pb free	Tube

ABSOLUTE MAXIMUM RATINGS ($T_C=25^\circ\text{C}$ unless otherwise noted)

Characteristics	Symbol	Rating		Unit
		SVF8N60T	SVF8N60F	
Drain-Source Voltage	V_{DS}	600		V
Gate-Source Voltage	V_{GS}	± 30		V
Drain Current	I_D	$T_C=25^\circ\text{C}$		A
		$T_C=100^\circ\text{C}$		
Drain Current Pulsed	I_{DM}	32.0		A
Power Dissipation($T_C=25^\circ\text{C}$) -Derate above 25°C	P_D	147	48	W
		1.18	0.38	W/ $^\circ\text{C}$
Single Pulsed Avalanche Energy (Note 1)	E_{AS}	450		mJ
Operation Junction Temperature Range	T_J	$-55 \sim +150$		$^\circ\text{C}$
Storage Temperature Range	T_{stg}	$-55 \sim +150$		$^\circ\text{C}$

THERMAL CHARACTERISTICS

Characteristics	Symbol	Rating		Unit
		SVF8N60T	SVF8N60F	
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	0.85	2.6	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	62.50	120	$^\circ\text{C}/\text{W}$

ELECTRICAL CHARACTERISTICS ($T_C=25^\circ\text{C}$ unless otherwise noted)

Characteristics	Symbol	Test conditions	Min.	Typ.	Max.	Unit
Drain -Source Breakdown Voltage	B_{VDSS}	$V_{GS}=0\text{V}, I_D=250\mu\text{A}$	600	--	--	V
Drain-Source Leakage Current	I_{DSS}	$V_{DS}=600\text{V}, V_{GS}=0\text{V}$	--	--	1.0	μA
Gate-Source Leakage Current	I_{GSS}	$V_{GS}=\pm 30\text{V}, V_{DS}=0\text{V}$	--	--	± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{GS}=V_{DS}, I_D=250\mu\text{A}$	2.0	--	4.0	V
Static Drain- Source On State Resistance	$R_{DS(on)}$	$V_{GS}=10\text{V}, I_D=4.0\text{A}$	--	0.96	1.2	Ω
Input Capacitance	C_{iss}	$V_{DS}=25\text{V}, V_{GS}=0\text{V},$ $f=1.0\text{MHZ}$	--	910	--	pF
Output Capacitance	C_{oss}		--	105	--	
Reverse Transfer Capacitance	C_{rss}		--	2.43	--	
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=300\text{V}, R_G=25\Omega,$ $I_D=8.0\text{A}$ (Note 2,3)	--	29.00	--	ns
Turn-on Rise Time	t_r		--	71.33	--	
Turn-off Delay Time	$t_{d(off)}$		--	34.93	--	
Turn-off Fall Time	t_f		--	32.80	--	
Total Gate Charge	Q_g	$V_{DS}=480\text{V}, I_D=8.0\text{A},$ $V_{GS}=10\text{V}$ (Note 2,3)	--	14.83	--	nC
Gate-Source Charge	Q_{gs}		--	5.90	--	
Gate-Drain Charge	Q_{gd}		--	4.00	--	

SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS

Characteristics	Symbol	Test conditions	Min.	Typ.	Max.	Unit
Continuous Source Current	I_S	Integral Reverse P-N Junction Diode in the MOSFET	--	--	8.0	A
Pulsed Source Current	I_{SM}		--	--	32.0	
Diode Forward Voltage	V_{SD}	$I_S=8.0A, V_{GS}=0V$	--	--	1.4	V
Reverse Recovery Time	T_{rr}	$I_S=8.0A, V_{GS}=0V,$ $di_F/dt=100A/\mu S$	--	520.65	--	ns
Reverse Recovery Charge	Q_{rr}		--	3.72	--	μC

Notes:

1. $L=30mH, I_{AS}=5.0A, V_{DD}=110V, R_G=25\Omega$, starting $T_J=25^\circ C$;
2. Pulse Test: Pulse width $\leq 300\mu s$, Duty cycle $\leq 2\%$;
3. Essentially independent of operating temperature.

TYPICAL CHARACTERISTICS

Figure 1. On-Region Characteristics

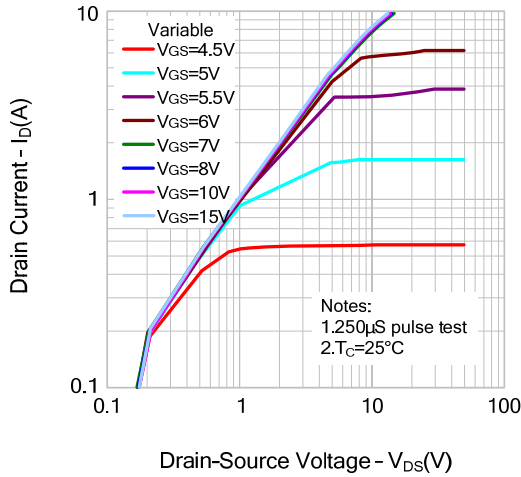


Figure 2. Transfer Characteristics

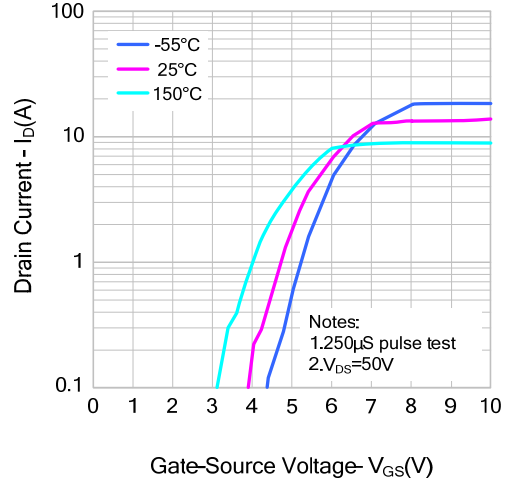


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

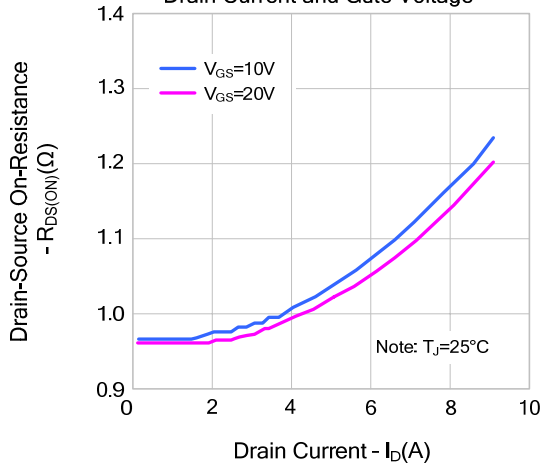


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

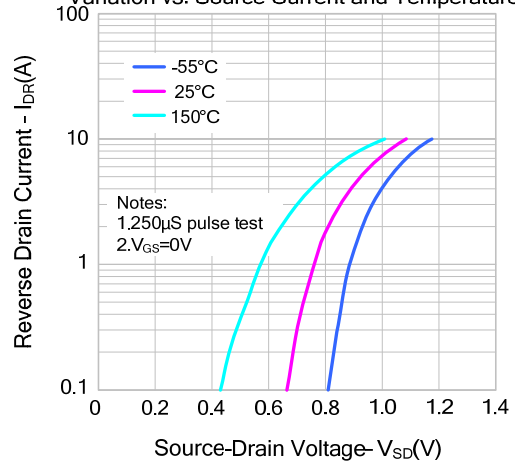


Figure 5. Capacitance Characteristics

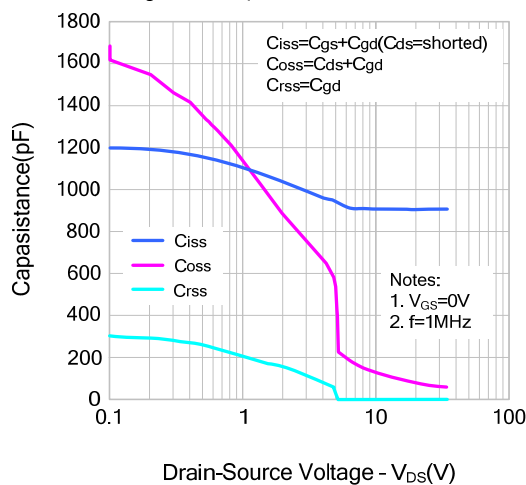
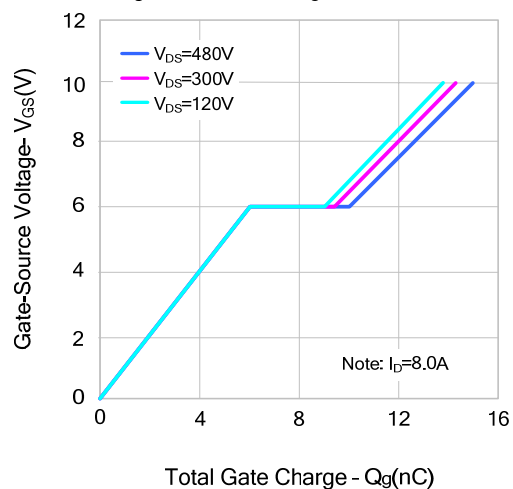


Figure 6. Gate Charge Characteristics



TYPICAL CHARACTERISTICS(continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

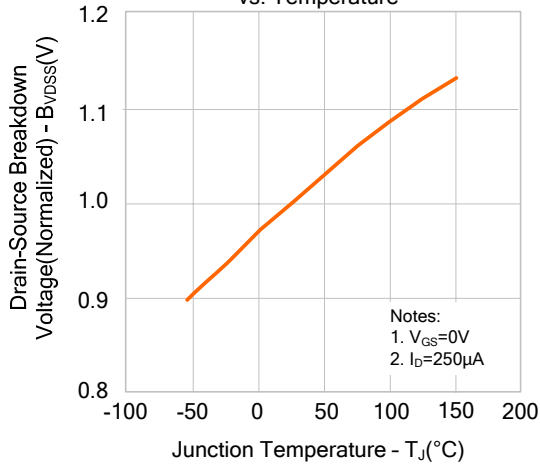


Figure 8. On-resistance Variation vs. Temperature

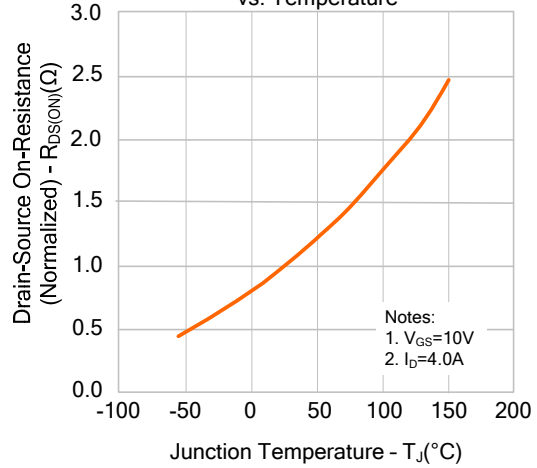


Figure 9-1. Max. Safe Operating Area(SVF8N60T)

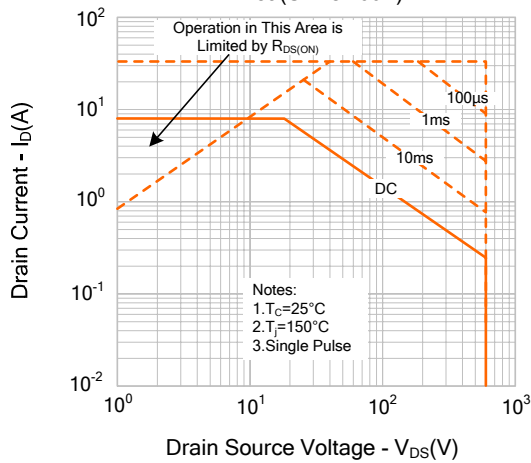


Figure 9-2. Max. Safe Operating Area(SVF8N60F)

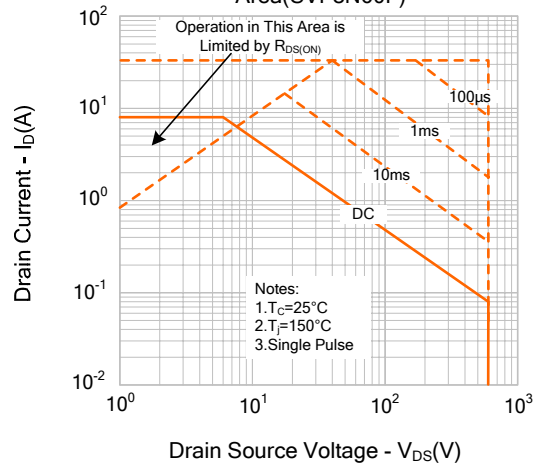
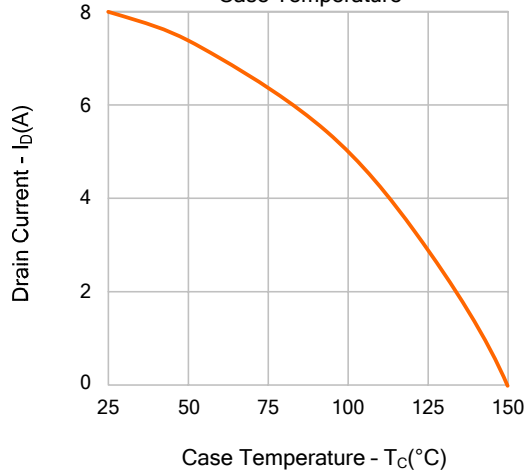
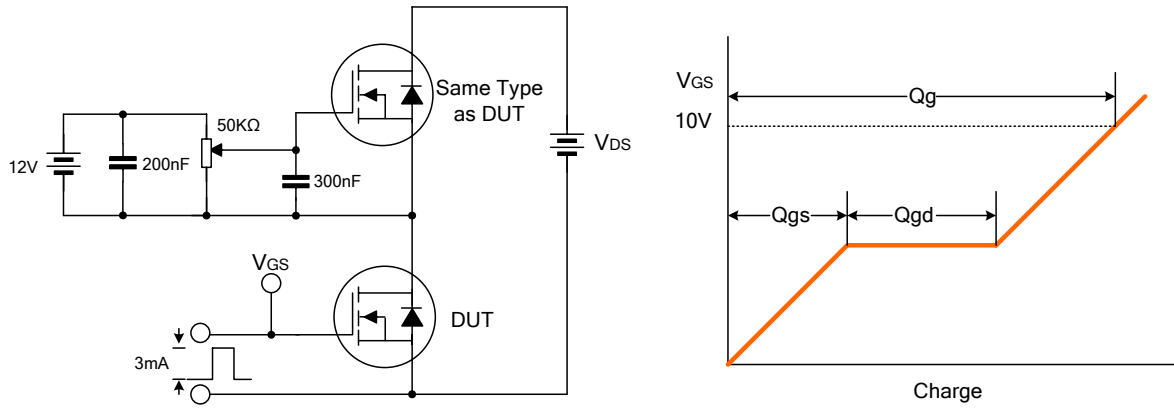


Figure 10. Maximum Drain Current vs. Case Temperature

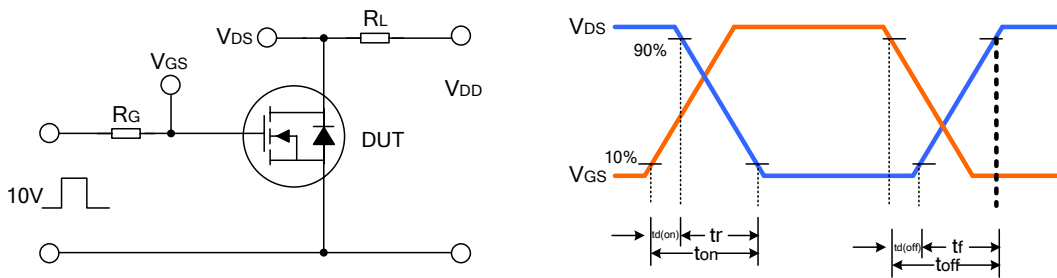


TYPICAL TEST CIRCUIT

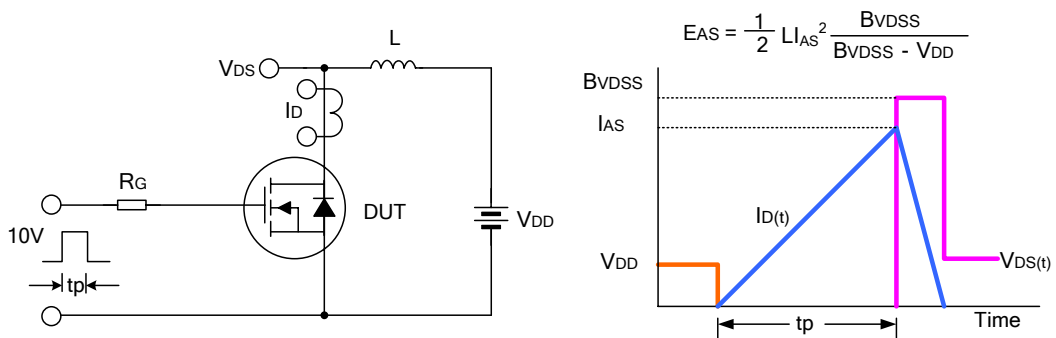
Gate Charge Test Circuit & Waveform



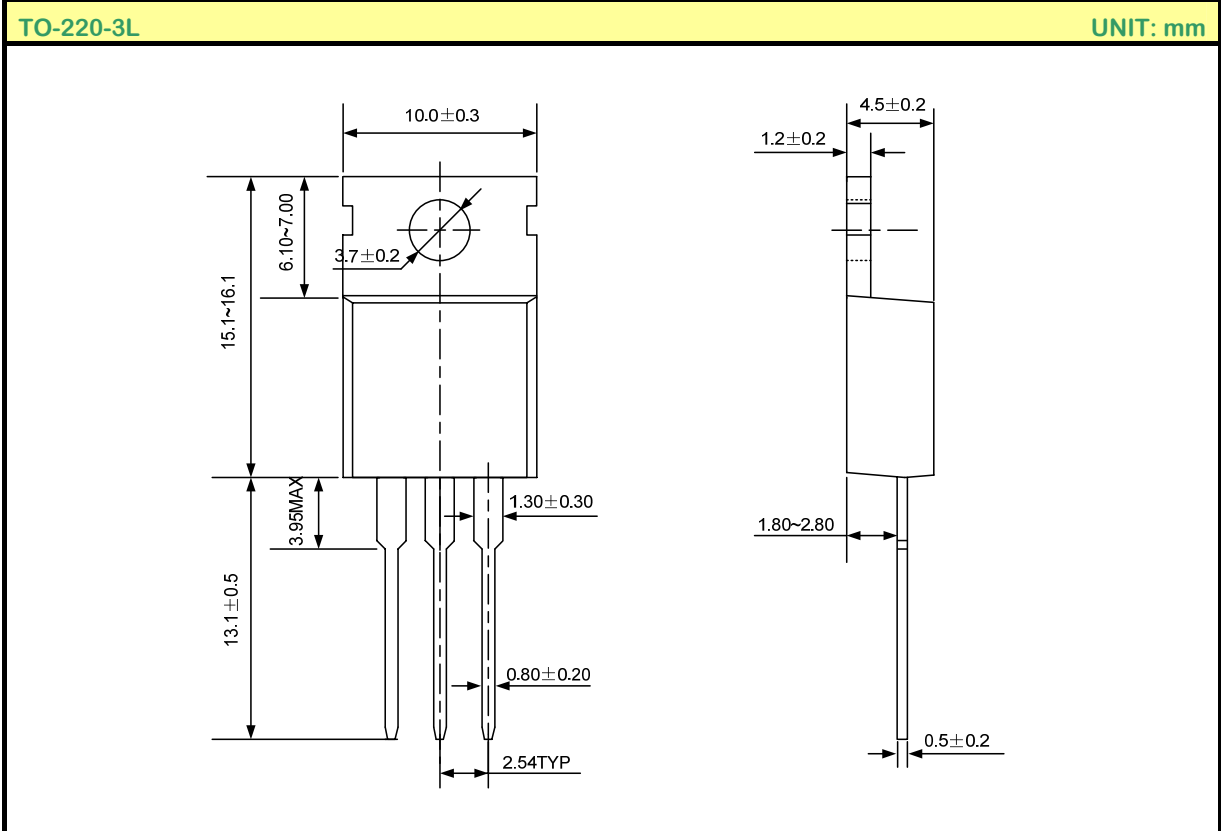
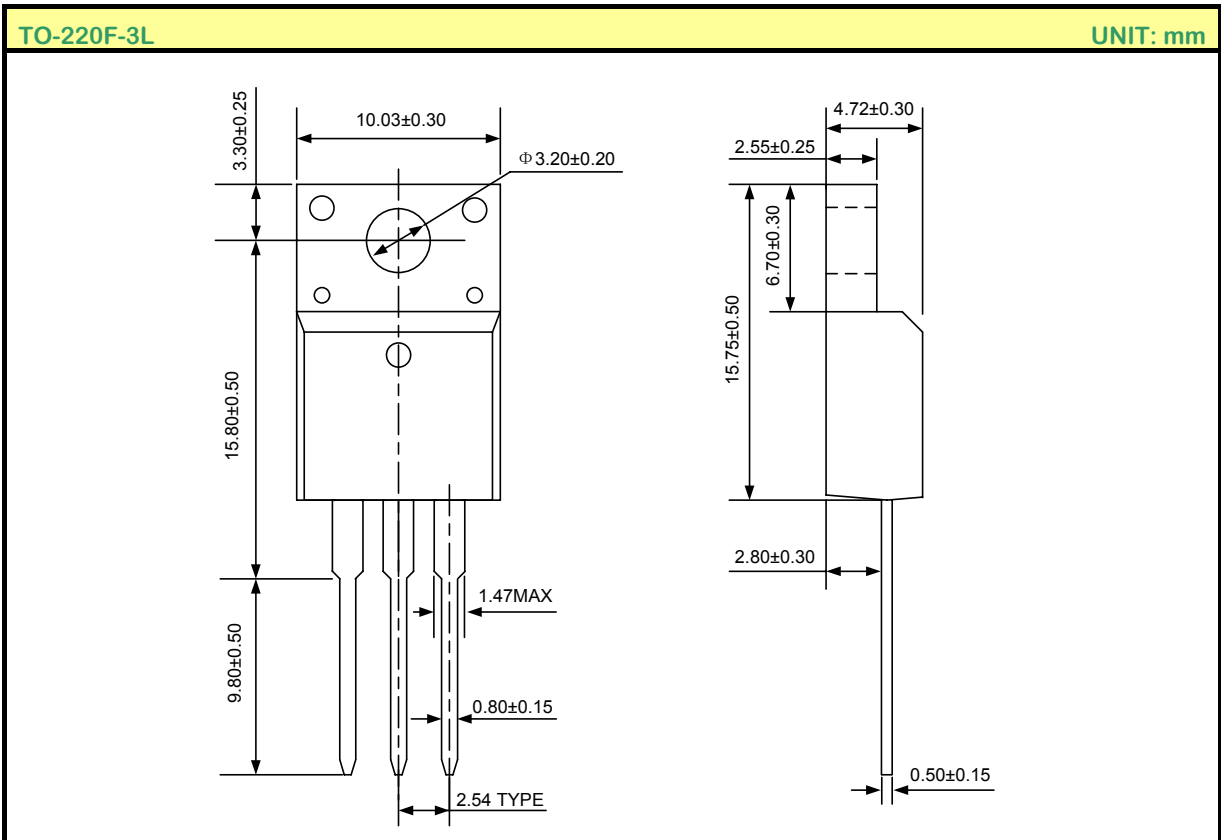
Resistive Switching Test Circuit & Waveform



Unclamped Inductive Switching Test Circuit & Waveform



PACKAGE OUTLINE





Disclaimer :

- Silan reserves the right to make changes to the information herein for the improvement of the design and performance without further notice! Customers should obtain the latest relevant information before placing orders and should verify that such information is complete and current.
- All semiconductor products malfunction or fail with some probability under special conditions. When using Silan products in system design or complete machine manufacturing, it is the responsibility of the buyer to comply with the safety standards strictly and take essential measures to avoid situations in which a malfunction or failure of such Silan products could cause loss of body injury or damage to property.
- Silan will supply the best possible product for customers!

ATTACHMENT

Revision History

Date	REV	Description	Page
2011.02.11	1.0	Original	
2011.08.30	1.1	Modify "PACKAGE OUTLINE"	
2012.06.04	1.2	Modify the values of T_{rr} and Q_{rr}	
2012.06.15	1.3	Modify the typ. value of $R_{DS(on)}$	